50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

31 August 2023

**Product data sheet** 

## 1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a medium power SOT1118 (DFN2020-6) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PIMN32PA PNP/PNP complement: PIMP32PA

#### 2. Features and benefits

- 500 mA output current capability
- Built-in resistors
- · Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs

# 3. Applications

- · Digital applications
- Cost-saving alternative to BC807 / BC817 series in digital applications
- · Control of IC inputs
- Switching loads

### 4. Quick reference data

#### Table 1. Quick reference data

Table 1. Quiek reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or					·	
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	500	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[2]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[2]	4.1	4.55	5	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR1
5	12	input (base) TR2		R2 R1
6	01	output (collector) TR1		
7	01	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN2020-6 (SOT1118)	GND1 I1 O2 aaa-007379

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PIMC32PA	DFN2020-6	plastic, leadless thermal enhanced ultra thin small outline package; no leads; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PIMC32PA	8F

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

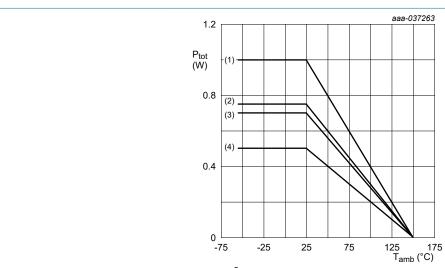
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or		'			
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	[1]	-	5	V
V <sub>I</sub>	input voltage		[1]	-5	12	V
Io	output current		[1]	-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	360	mW
			[3]	-	550	mW
			[4]	-	510	mW
			[5]	-	730	mW
Per device	<u> </u>		'		'	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	500	mW
			[3]	-	750	mW
			[4]	-	700	mW
			[5]	-	1	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided, 35µm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>. [3]
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>. [5]



- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided, 35µm copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided, 35µm copper, standard footprint

Per device: Power derating curves for DFN2020-6 (SOT1118)

PIMC32PA

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50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor				<b>-</b>		
() ~/	thermal resistance from	in free air	[1]	-	-	348	K/W
	junction to ambient	[2] [3] [4]	[2]	-	-	228	K/W
			[3]	-	-	246	K/W
			[4]	-	-	172	K/W
Per device			'		,		
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	[1]	-	-	250	K/W	
			[2]	-	-	167	K/W
			[3]	-	-	179	K/W
			[4]	-	-	125	K/W

- Device mounted on an FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint.
- [2] [3] Device mounted on an FR4 PCB, single-sided, 35μm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

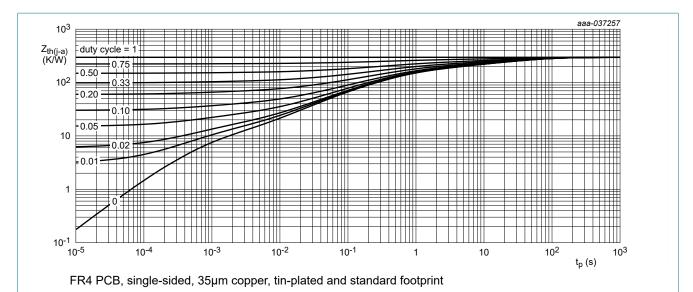
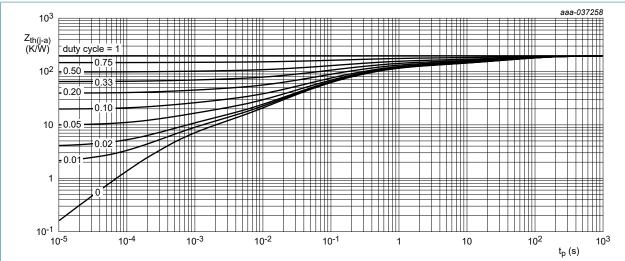


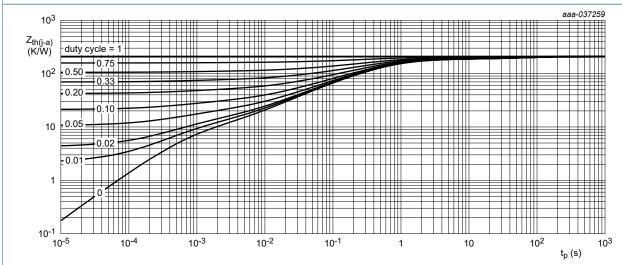
Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



FR4 PCB, single-sided, 35µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

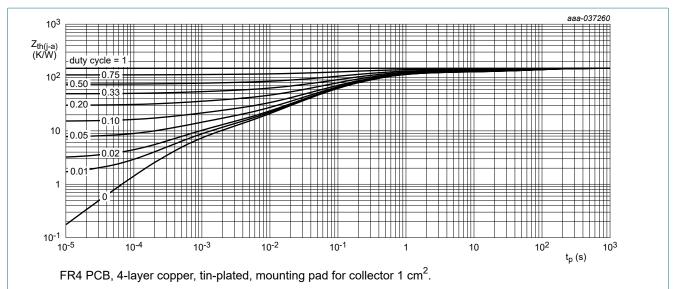


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

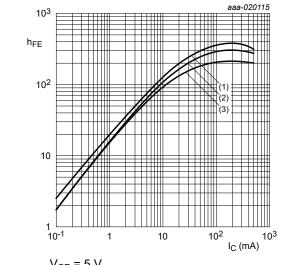
# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	0.65	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	[1]	70	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	0.4	0.65	1	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C	[1]	0.5	0.95	1.4	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[2]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[2]	4.1	4.55	5	
TR1 (NPN)					·	'	·
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	5	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[3]	-	210	-	MHz
TR2 (PNP)				'			
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	7	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[3]	-	150	-	MHz
	<del>.</del>					_	

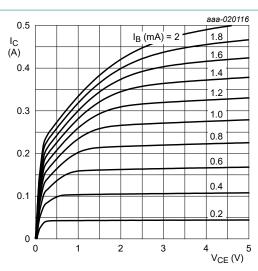
For the PNP transistor with negative polarity. See section "Test information" for resistor calculation and test conditions. Characteristics of built-in transistor.

#### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



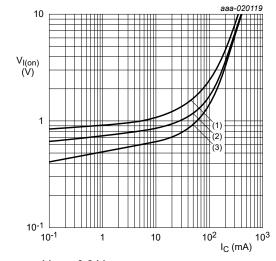
V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 6. collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 7. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



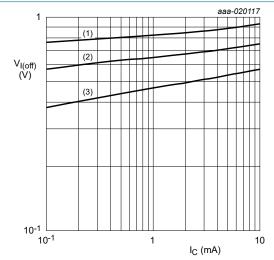
 $V_{CE}$  = 0.3 V

(1) T<sub>amb</sub> = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 100 °C

Fig. 8. TR1 (NPN): On-state input voltage as a function | Fig. 9. of collector current; typical values



 $V_{CE} = 5 V$ 

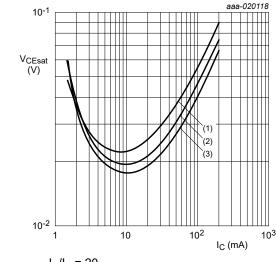
(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

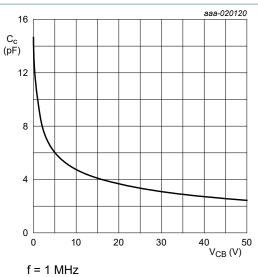
### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



 $I_{\rm C}/I_{\rm B} = 20$ 

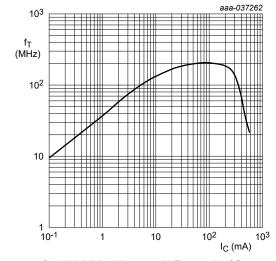
(1)  $T_{amb} = 100 \text{ °C}$ (2)  $T_{amb} = 25 \text{ °C}$ (3)  $T_{amb} = -40 \text{ °C}$ 

Fig. 10. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



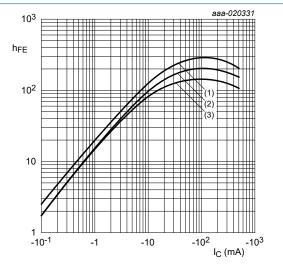
 $T_{amb}$  = 25 °C

Fig. 11. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz;  $V_{CE} = -5 \text{ V T}_{amb} = 25 ^{\circ}\text{C}$ 

Fig. 12. TR2 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE}$  = -5 V

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 13. TR2 (PNP): DC current gain as a function of collector current; typical values

#### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

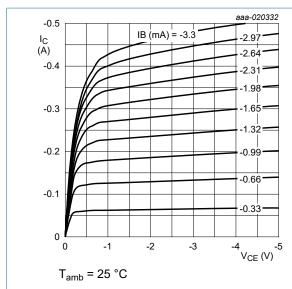
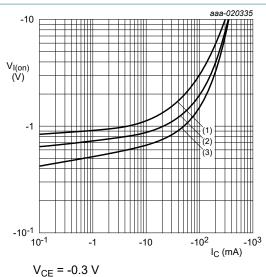
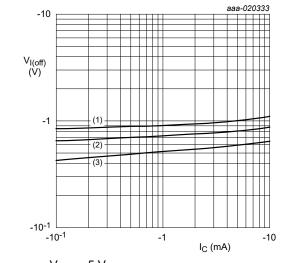


Fig. 14. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



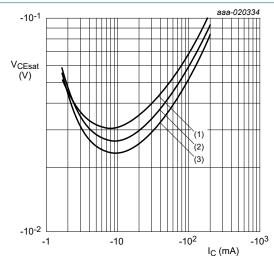
V<sub>CE</sub> = -0.3 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 15. TR2 (PNP): On-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 V$ (1)  $T_{amb} = -40 \, ^{\circ}C$ (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = 100 \, ^{\circ}C$ 

of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) T<sub>amb</sub> = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 16. TR2 (PNP): Off-state input voltage as a function | Fig. 17. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

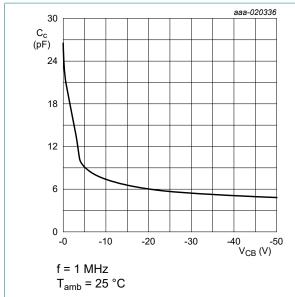


Fig. 18. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

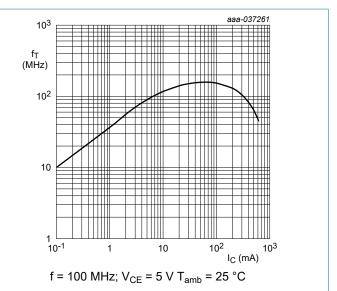


Fig. 19. TR1 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

# 11. Test information

#### **Resistor calculation**

• Calculation of bias resistor 1 (R1):

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

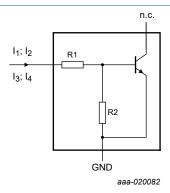


Fig. 20. NPN transistor: Resistor test circuit

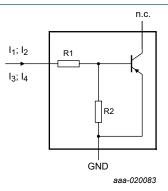


Fig. 21. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

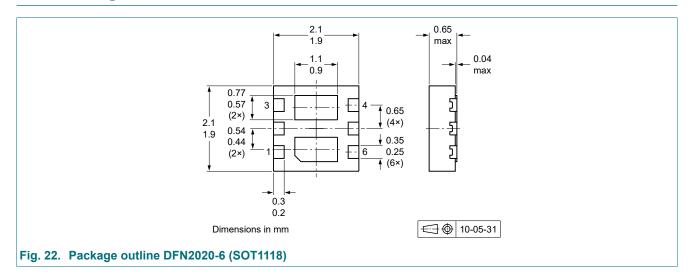
**Table 8. Resistor test conditions** 

PIMC32PA	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14
TR1 (NPN)	2.2	10	0.7 mA	0.8 mA	-0.45 mA	-0.55 mA
TR2 (PNP)			-0.7 mA	-0.8 mA	0.45 mA	0.55 mA

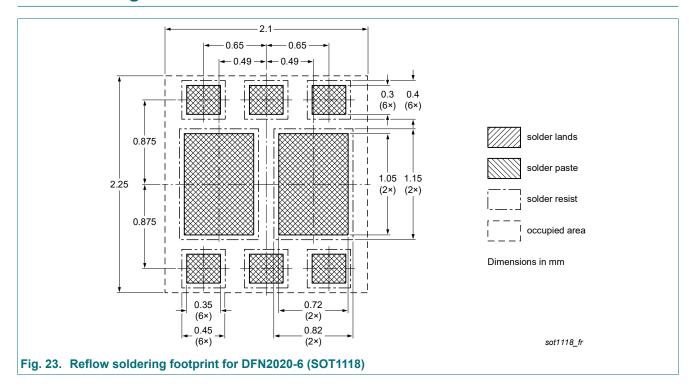
PIMC32PA

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

# 12. Package outline



# 13. Soldering



50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMC32PA v.1	20230831	Product data sheet	-	-

#### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PIMC32PA

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### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

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